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Understanding Embedded - CPLDs (Complex Programmable Logic Devices)

Embedded - CPLDs, or Complex Programmable Logic Devices, are highly versatile digital logic devices used in electronic systems. These programmable components are designed to perform complex logical operations and can be customized for specific applications. Unlike fixed-function ICs, CPLDs offer the flexibility to reprogram their configuration, making them an ideal choice for various embedded systems. They consist of a set of logic gates and programmable interconnects, allowing designers to implement complex logic circuits without needing custom hardware.

Applications of Embedded - CPLDs

Details	
Product Status	Active
Programmable Type	In System Programmable
Delay Time tpd(1) Max	5.4 ns
Voltage Supply - Internal	2.5V, 3.3V
Number of Logic Elements/Blocks	570
Number of Macrocells	440
Number of Gates	-
Number of I/O	116
Operating Temperature	0°C ~ 85°C (TJ)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epm570t144c5n

1. Introduction

MII51001-1.9

Introduction

The MAX® II family of instant-on, non-volatile CPLDs is based on a 0.18-µm, 6-layer-metal-flash process, with densities from 240 to 2,210 logic elements (LEs) (128 to 2,210 equivalent macrocells) and non-volatile storage of 8 Kbits. MAX II devices offer high I/O counts, fast performance, and reliable fitting versus other CPLD architectures. Featuring MultiVolt core, a user flash memory (UFM) block, and enhanced in-system programmability (ISP), MAX II devices are designed to reduce cost and power while providing programmable solutions for applications such as bus bridging, I/O expansion, power-on reset (POR) and sequencing control, and device configuration control.

Features

The MAX II CPLD has the following features:

- Low-cost, low-power CPLD
- Instant-on, non-volatile architecture
- Standby current as low as 25 µA
- Provides fast propagation delay and clock-to-output times
- Provides four global clocks with two clocks available per logic array block (LAB)
- UFM block up to 8 Kbits for non-volatile storage
- MultiVolt core enabling external supply voltages to the device of either 3.3 V/2.5 V or 1.8 V
- MultiVolt I/O interface supporting 3.3-V, 2.5-V, 1.8-V, and 1.5-V logic levels
- Bus-friendly architecture including programmable slew rate, drive strength, bus-hold, and programmable pull-up resistors
- Schmitt triggers enabling noise tolerant inputs (programmable per pin)
- I/Os are fully compliant with the Peripheral Component Interconnect Special Interest Group (PCI SIG) PCI Local Bus Specification, Revision 2.2 for 3.3-V operation at 66 MHz
- Supports hot-socketing
- Built-in Joint Test Action Group (JTAG) boundary-scan test (BST) circuitry compliant with IEEE Std. 1149.1-1990
- ISP circuitry compliant with IEEE Std. 1532

MAX II devices are available in space-saving FineLine BGA, Micro FineLine BGA, and thin quad flat pack (TQFP) packages (refer to Table 1–3 and Table 1–4). MAX II devices support vertical migration within the same package (for example, you can migrate between the EPM570, EPM1270, and EPM2210 devices in the 256-pin FineLine BGA package). Vertical migration means that you can migrate to devices whose dedicated pins and JTAG pins are the same and power pins are subsets or supersets for a given package across device densities. The largest density in any package has the highest number of power pins; you must lay out for the largest planned density in a package to provide the necessary power pins for migration. For I/O pin migration across densities, cross reference the available I/O pins using the device pin-outs for all planned densities of a given package type to identify which I/O pins can be migrated. The Quartus® II software can automatically cross-reference and place all pins for you when given a device migration list.

Table 1–3. MAX II Packages and User I/O Pins

Device	68-Pin Micro FineLine BGA *(1)*	100-Pin Micro FineLine BGA *(1)*	100-Pin FineLine BGA	100-Pin TQFP	144-Pin TQFP	144-Pin Micro FineLine BGA *(1)*	256-Pin Micro FineLine BGA *(1)*	256-Pin FineLine BGA	324-Pin FineLine BGA
EPM240 EPM240G	—	80	80	80	—	—	—	—	—
EPM570 EPM570G	—	76	76	76	116	—	160	160	—
EPM1270 EPM1270G	—	—	—	—	116	—	212	212	—
EPM2210 EPM2210G	—	—	—	—	—	—	—	204	272
EPM240Z	54	80	—	—	—	—	—	—	—
EPM570Z	—	76	—	—	—	116	160	—	—

Note to Table 1–3:

(1) Packages available in lead-free versions only.

Table 1–4. MAX II TQFP, FineLine BGA, and Micro FineLine BGA Package Sizes

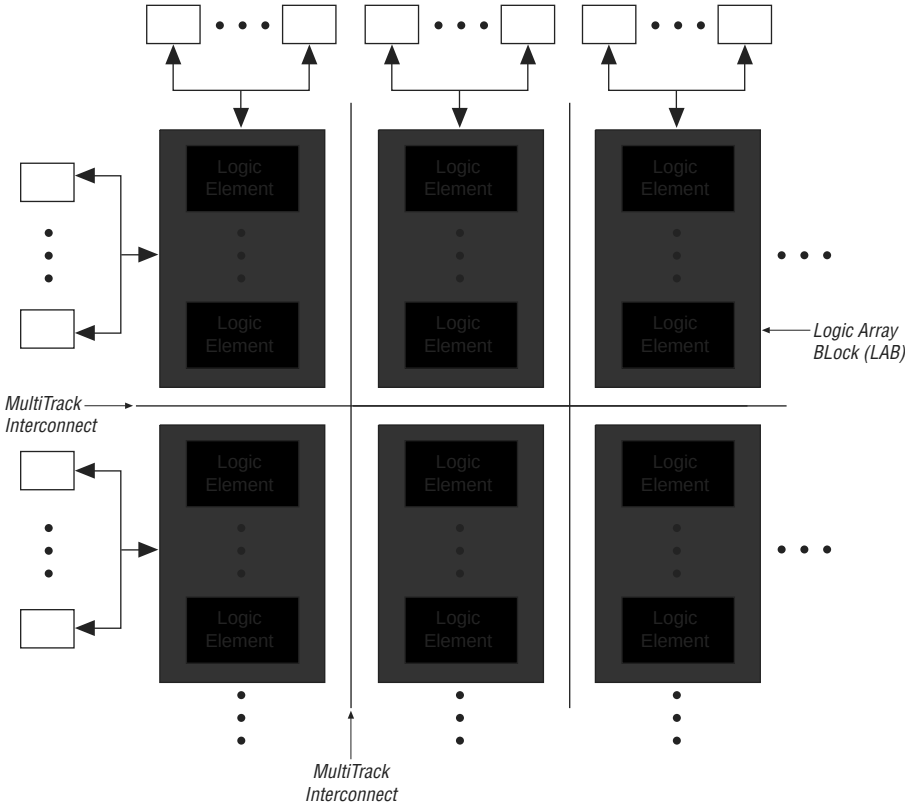
Package	68-Pin Micro FineLine BGA	100-Pin Micro FineLine BGA	100-Pin FineLine BGA	100-Pin TQFP	144-Pin TQFP	144-Pin Micro FineLine BGA	256-Pin Micro FineLine BGA	256-Pin FineLine BGA	324-Pin FineLine BGA
Pitch (mm)	0.5	0.5	1	0.5	0.5	0.5	0.5	1	1
Area (mm2)	25	36	121	256	484	49	121	289	361
Length × width (mm × mm)	5 × 5	6 × 6	11 × 11	16 × 16	22 × 22	7 × 7	11 × 11	17 × 17	19 × 19

Table 1–6. Document Revision History

Date and Revision	Changes Made	Summary of Changes
June 2005, version 1.3	■ Updated timing numbers in Table 1-1.	—
December 2004, version 1.2	■ Updated timing numbers in Table 1-1.	—
June 2004, version 1.1	■ Updated timing numbers in Table 1-1.	—

Figure 2–1 shows a functional block diagram of the MAX II device.

Figure 2–1. MAX II Device Block Diagram



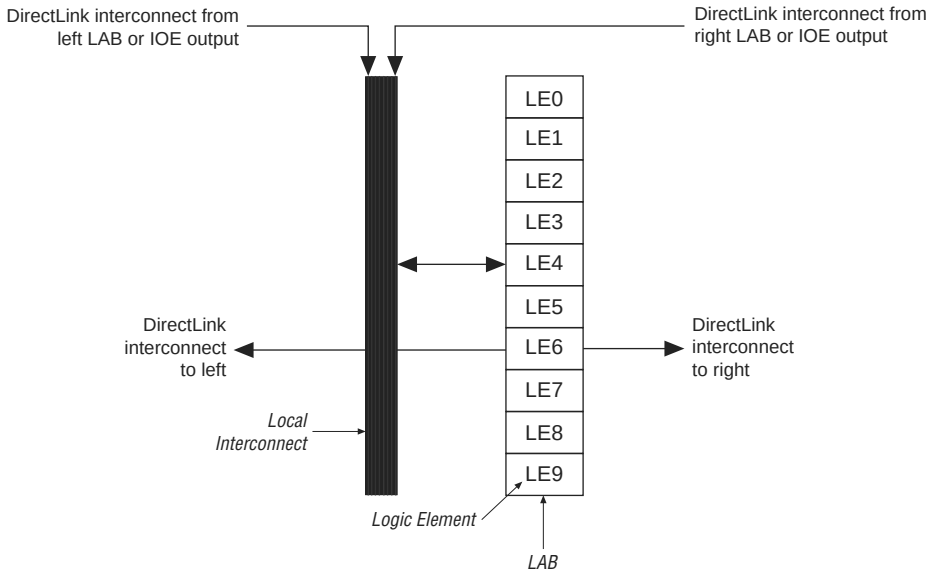
Each MAX II device contains a flash memory block within its floorplan. On the EPM240 device, this block is located on the left side of the device. On the EPM570, EPM1270, and EPM2210 devices, the flash memory block is located on the bottom-left area of the device. The majority of this flash memory storage is partitioned as the dedicated configuration flash memory (CFM) block. The CFM block provides the non-volatile storage for all of the SRAM configuration information. The CFM automatically downloads and configures the logic and I/O at power-up, providing instant-on operation.

For more information about configuration upon power-up, refer to the *Hot Socketing and Power-On Reset in MAX II Devices* chapter in the *MAX II Device Handbook*.

A portion of the flash memory within the MAX II device is partitioned into a small block for user data. This user flash memory (UFM) block provides 8,192 bits of general-purpose user storage. The UFM provides programmable port connections to the logic array for reading and writing. There are three LAB rows adjacent to this block, with column numbers varying by device.

Table 2–1 shows the number of LAB rows and columns in each device, as well as the number of LAB rows and columns adjacent to the flash memory area in the EPM570, EPM1270, and EPM2210 devices. The long LAB rows are full LAB rows that extend from one side of row I/O blocks to the other. The short LAB rows are adjacent to the UFM block; their length is shown as width in LAB columns.

Figure 2–4. DirectLink Connection



LAB Control Signals

Each LAB contains dedicated logic for driving control signals to its LEs. The control signals include two clocks, two clock enables, two asynchronous clears, a synchronous clear, an asynchronous preset/load, a synchronous load, and add/subtract control signals, providing a maximum of 10 control signals at a time. Although synchronous load and clear signals are generally used when implementing counters, they can also be used with other functions.

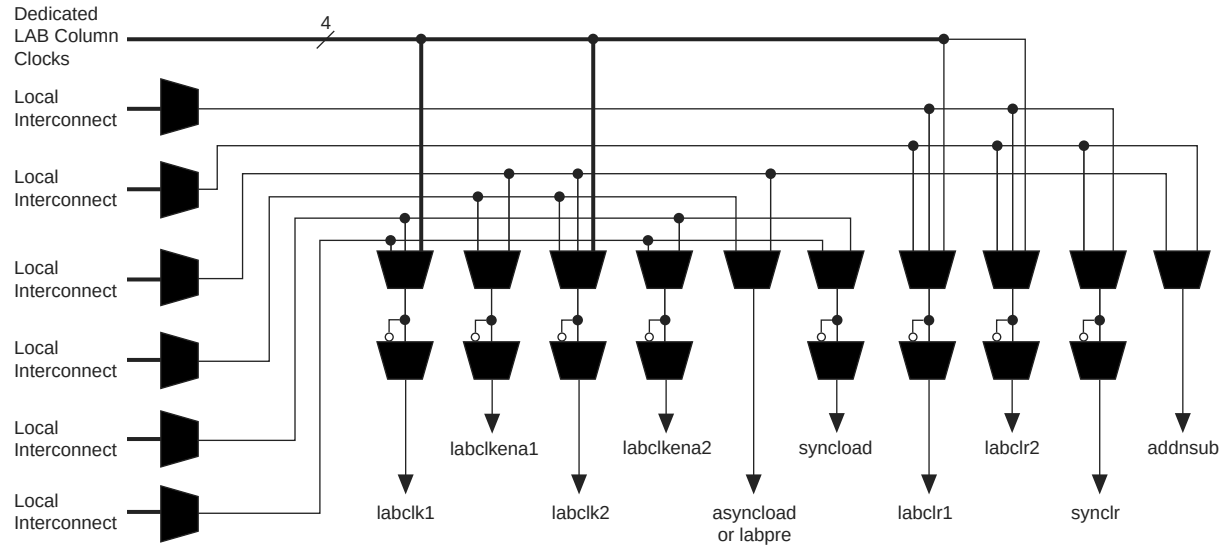
Each LAB can use two clocks and two clock enable signals. Each LAB's clock and clock enable signals are linked. For example, any LE in a particular LAB using the `labclk1` signal also uses `labclkena1`. If the LAB uses both the rising and falling edges of a clock, it also uses both LAB-wide clock signals. Deasserting the clock enable signal turns off the LAB-wide clock.

Each LAB can use two asynchronous clear signals and an asynchronous load/preset signal. By default, the Quartus II software uses a `NOT` gate push-back technique to achieve preset. If you disable the `NOT` gate push-back option or assign a given register to power-up high using the Quartus II software, the preset is then achieved using the asynchronous load signal with asynchronous load data input tied high.

With the LAB-wide addnsub control signal, a single LE can implement a one-bit adder and subtractor. This saves LE resources and improves performance for logic functions such as correlators and signed multipliers that alternate between addition and subtraction depending on data.

The LAB column clocks [3..0], driven by the global clock network, and LAB local interconnect generate the LAB-wide control signals. The MultiTrack interconnect structure drives the LAB local interconnect for non-global control signal generation. The MultiTrack interconnect's inherent low skew allows clock and control signal distribution in addition to data. Figure 2–5 shows the LAB control signal generation circuit.

Figure 2–5. LAB-Wide Control Signals



Logic Elements

The smallest unit of logic in the MAX II architecture, the LE, is compact and provides advanced features with efficient logic utilization. Each LE contains a four-input LUT, which is a function generator that can implement any function of four variables. In addition, each LE contains a programmable register and carry chain with carry-select capability. A single LE also supports dynamic single-bit addition or subtraction mode selectable by an LAB-wide control signal. Each LE drives all types of interconnects: local, row, column, LUT chain, register chain, and DirectLink interconnects. See Figure 2–6.

The Quartus II software automatically creates carry chain logic during design processing, or you can create it manually during design entry. Parameterized functions such as LPM functions automatically take advantage of carry chains for the appropriate functions. The Quartus II software creates carry chains longer than 10 LEs by linking adjacent LABs within the same row together automatically. A carry chain can extend horizontally up to one full LAB row, but does not extend between LAB rows.

Clear and Preset Logic Control

LAB-wide signals control the logic for the register's clear and preset signals. The LE directly supports an asynchronous clear and preset function. The register preset is achieved through the asynchronous load of a logic high. MAX II devices support simultaneous preset/asynchronous load and clear signals. An asynchronous clear signal takes precedence if both signals are asserted simultaneously. Each LAB supports up to two clears and one preset signal.

In addition to the clear and preset ports, MAX II devices provide a chip-wide reset pin (DEV_CLRn) that resets all registers in the device. An option set before compilation in the Quartus II software controls this pin. This chip-wide reset overrides all other control signals and uses its own dedicated routing resources (that is, it does not use any of the four global resources). Driving this signal low before or during power-up prevents user mode from releasing clears within the design. This allows you to control when clear is released on a device that has just been powered-up. If not set for its chip-wide reset function, the DEV_CLRn pin is a regular I/O pin.

By default, all registers in MAX II devices are set to power-up low. However, this power-up state can be set to high on individual registers during design entry using the Quartus II software.

MultiTrack Interconnect

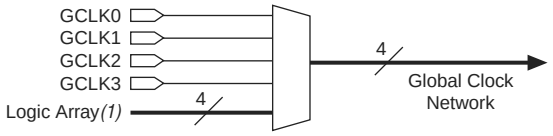
In the MAX II architecture, connections between LEs, the UFM, and device I/O pins are provided by the MultiTrack interconnect structure. The MultiTrack interconnect consists of continuous, performance-optimized routing lines used for inter- and intra-design block connectivity. The Quartus II Compiler automatically places critical design paths on faster interconnects to improve design performance.

The MultiTrack interconnect consists of row and column interconnects that span fixed distances. A routing structure with fixed length resources for all devices allows predictable and short delays between logic levels instead of large delays associated with global or long routing lines. Dedicated row interconnects route signals to and from LABs within the same row. These row resources include:

- DirectLink interconnects between LABs
- R4 interconnects traversing four LABs to the right or left

The DirectLink interconnect allows an LAB to drive into the local interconnect of its left and right neighbors. The DirectLink interconnect provides fast communication between adjacent LABs and/or blocks without using row interconnect resources.

Figure 2–13. Global Clock Generation

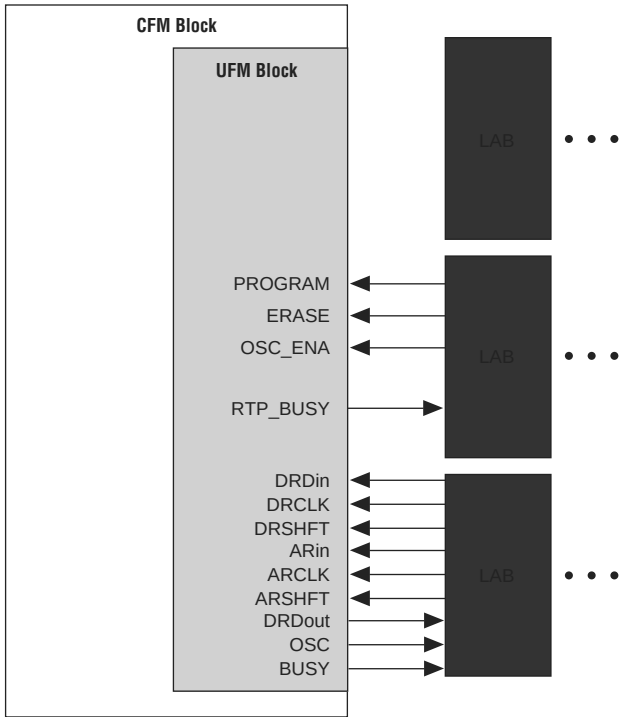


Note to Figure 2–13:

(1) Any I/O pin can use a MultiTrack interconnect to route as a logic array-generated global clock signal.

The global clock network drives to individual LAB column signals, LAB column clocks [3..0], that span an entire LAB column from the top to the bottom of the device. Unused global clocks or control signals in a LAB column are turned off at the LAB column clock buffers shown in Figure 2–14. The LAB column clocks [3..0] are multiplexed down to two LAB clock signals and one LAB clear signal. Other control signal types route from the global clock network into the LAB local interconnect. See "LAB Control Signals" on page 2–5 for more information.

Figure 2–16. EPM240 UFM Block LAB Row Interface *(Note 1)*



Note to Figure 2–16:

(1) The UFM block inputs and outputs can drive to/from all types of interconnects, not only DirectLink interconnects from adjacent row LABs.

IEEE 1532 Support

The JTAG circuitry and ISP instruction set in MAX II devices is compliant to the IEEE 1532-2002 programming specification. This provides industry-standard hardware and software for in-system programming among multiple vendor programmable logic devices (PLDs) in a JTAG chain.

The MAX II 1532 BSDL files will be released on the Altera website when available.

Jam Standard Test and Programming Language (STAPL)

The Jam STAPL JEDEC standard, JESD71, can be used to program MAX II devices with in-circuit testers, PCs, or embedded processors. The Jam byte code is also supported for MAX II devices. These software programming protocols provide a compact embedded solution for programming MAX II devices.

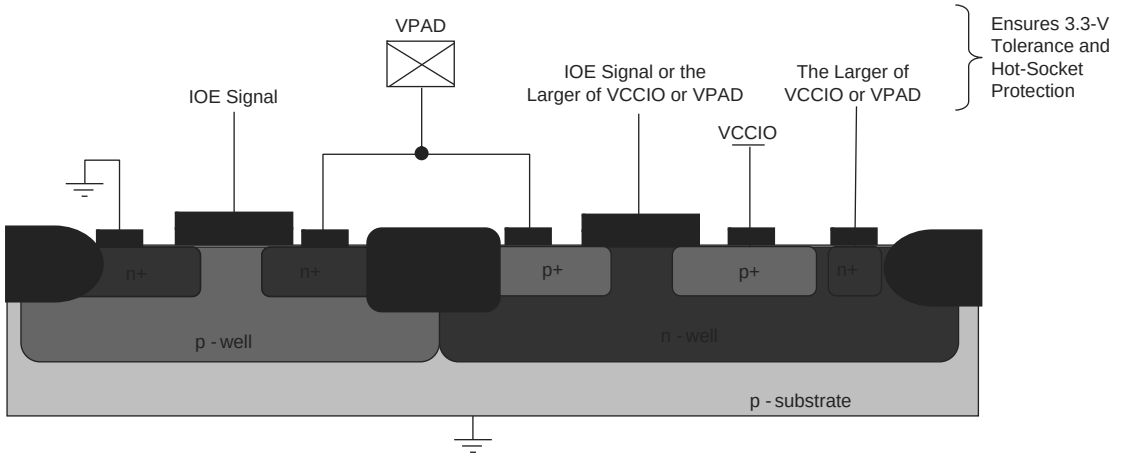
For more information, refer to the *Using Jam STAPL for ISP via an Embedded Processor* chapter in the *MAX II Device Handbook*.

Programming Sequence

During in-system programming, 1532 instructions, addresses, and data are shifted into the MAX II device through the `TDI` input pin. Data is shifted out through the `TDO` output pin and compared against the expected data. Programming a pattern into the device requires the following six ISP steps. A stand-alone verification of a programmed pattern involves only stages 1, 2, 5, and 6. These steps are automatically executed by third-party programmers, the Quartus II software, or the Jam STAPL and Jam Byte-Code Players.

1. *Enter ISP*—The enter ISP stage ensures that the I/O pins transition smoothly from user mode to ISP mode.
2. *Check ID*—Before any program or verify process, the silicon ID is checked. The time required to read this silicon ID is relatively small compared to the overall programming time.
3. *Sector Erase*—Erasing the device in-system involves shifting in the instruction to erase the device and applying an erase pulse(s). The erase pulse is automatically generated internally by waiting in the run/test/idle state for the specified erase pulse time of 500 ms for the CFM block and 500 ms for each sector of the UFM block.
4. *Program*—Programming the device in-system involves shifting in the address, data, and program instruction and generating the program pulse to program the flash cells. The program pulse is automatically generated internally by waiting in the run/test/idle state for the specified program pulse time of 75 µs. This process is repeated for each address in the CFM and UFM blocks.
5. *Verify*—Verifying a MAX II device in-system involves shifting in addresses, applying the verify instruction to generate the read pulse, and shifting out the data for comparison. This process is repeated for each CFM and UFM address.
6. *Exit ISP*—An exit ISP stage ensures that the I/O pins transition smoothly from ISP mode to user mode.

Figure 4–2. Transistor-Level Diagram of MAX II Device I/O Buffers



The CMOS output drivers in the I/O pins intrinsically provide electrostatic discharge (ESD) protection. There are two cases to consider for ESD voltage strikes: positive voltage zap and negative voltage zap.

A positive ESD voltage zap occurs when a positive voltage is present on an I/O pin due to an ESD charge event. This can cause the N+ (Drain)/ P-Substrate junction of the N-channel drain to break down and the N+ (Drain)/P-Substrate/N+ (Source) intrinsic bipolar transistor turn on to discharge ESD current from I/O pin to GND. The dashed line (see Figure 4–3) shows the ESD current discharge path during a positive ESD zap.

Figure 4–3. ESD Protection During Positive Voltage Zap

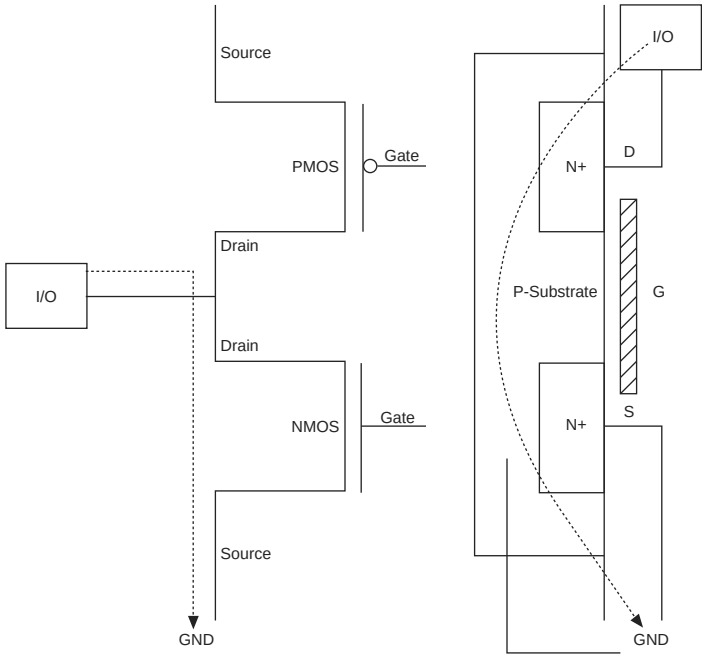
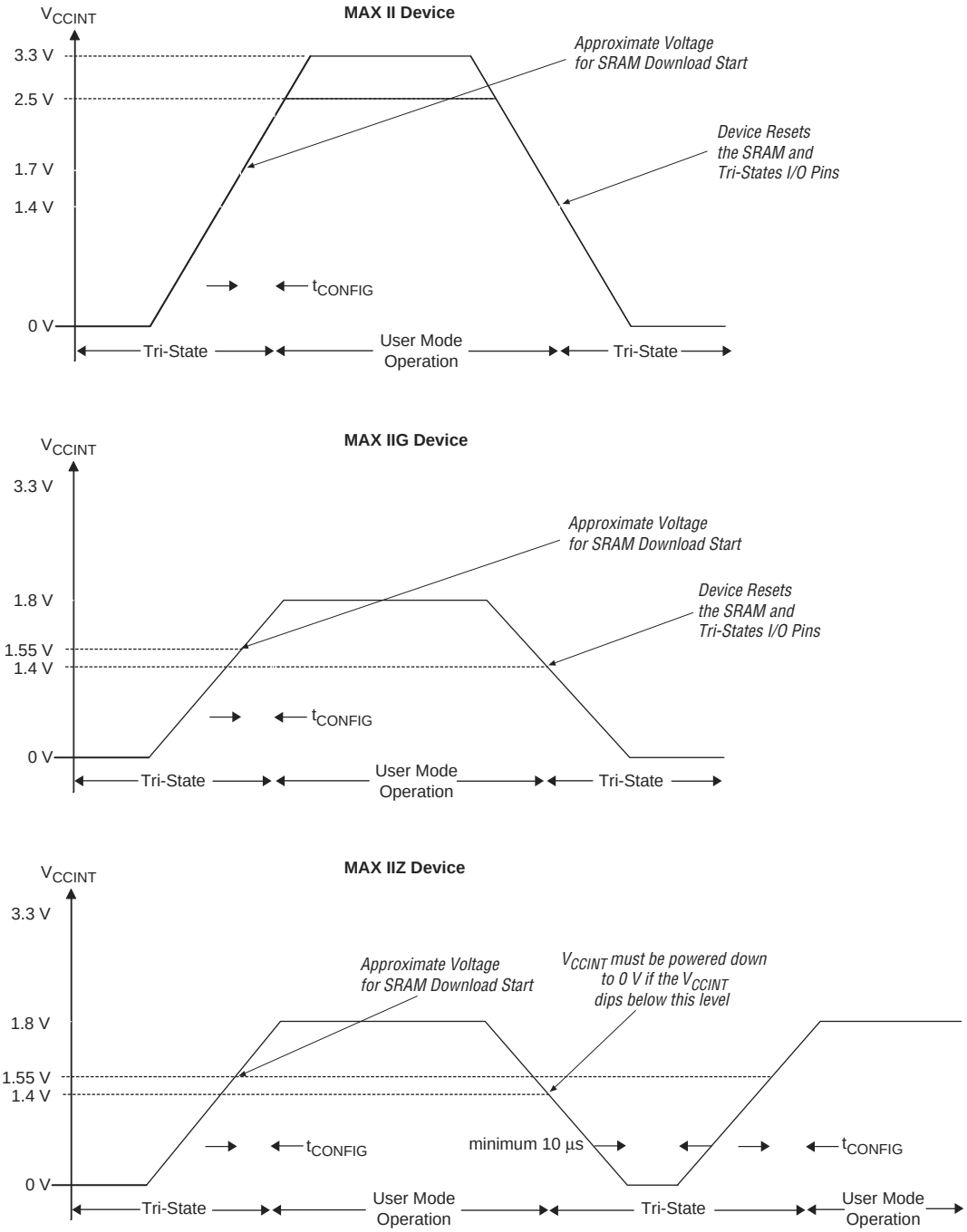


Figure 4–5. Power-Up Characteristics for MAX II, MAX IIG, and MAX IIZ Devices *(Note 1), (2)*



Notes to Figure 4–5:

(1) Time scale is relative.

(2) Figure 4–5 assumes all V_{CCIO} banks power up simultaneously with the V_{CCINT} profile shown. If not, t_{CONFIG} stretches out until all V_{CCIO} banks are powered.

☞ After SRAM configuration, all registers in the device are cleared and released into user function before I/O tri-states are released. To release clears after tri-states are released, use the DEV_CLRn pin option. To hold the tri-states beyond the power-up configuration time, use the DEV_OE pin option.

Programming/Erasure Specifications

Table 5–3 shows the MAX II device family programming/erasure specifications.

Table 5–3. MAX II Device Programming/Erasure Specifications

Parameter	Minimum	Typical	Maximum	Unit
Erase and reprogram cycles	—	—	100 *(1)*	Cycles

Note to Table 5–3:

(1) This specification applies to the UFM and configuration flash memory (CFM) blocks.

DC Electrical Characteristics

Table 5–4 shows the MAX II device family DC electrical characteristics.

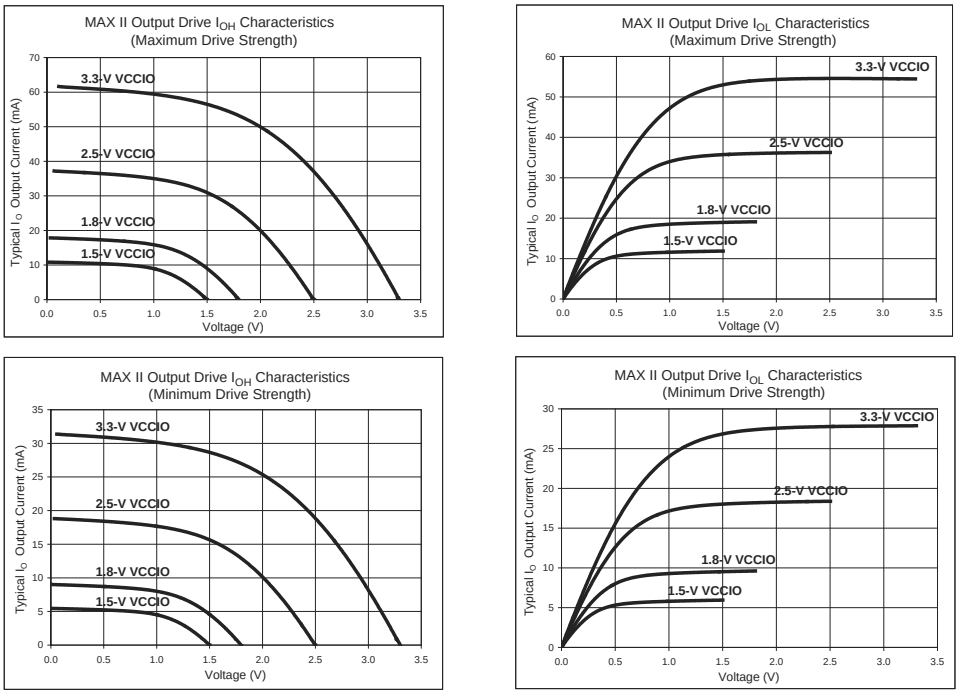
Table 5–4. MAX II Device DC Electrical Characteristics *(Note 1)* (Part 1 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
I_I	Input pin leakage current	$V_I = V_{CCIO}$ max to 0 V *(2)*	–10	—	10	µA
I_{OZ}	Tri-stated I/O pin leakage current	$V_O = V_{CCIO}$ max to 0 V *(2)*	–10	—	10	µA
$I_{CCSTANDBY}$	V_{CCINT} supply current (standby) *(3)*	MAX II devices	—	12	—	mA
		MAX IIG devices	—	2	—	mA
		EPM240Z (Commercial grade) *(4)*	—	25	90	µA
		EPM240Z (Industrial grade) *(5)*	—	25	139	µA
		EPM570Z (Commercial grade) *(4)*	—	27	96	µA
		EPM570Z (Industrial grade) *(5)*	—	27	152	µA
$V_{SCHMITT}$ *(6)*	Hysteresis for Schmitt trigger input *(7)*	V_{CCIO} = 3.3 V	—	400	—	mV
		V_{CCIO} = 2.5 V	—	190	—	mV
$I_{CCPOWERUP}$	V_{CCINT} supply current during power-up *(8)*	MAX II devices	—	55	—	mA
		MAX IIG and MAX IIZ devices	—	40	—	mA
R_{PULLUP}	Value of I/O pin pull-up resistor during user mode and in-system programming	V_{CCIO} = 3.3 V *(9)*	5	—	25	kΩ
		V_{CCIO} = 2.5 V *(9)*	10	—	40	kΩ
		V_{CCIO} = 1.8 V *(9)*	25	—	60	kΩ
		V_{CCIO} = 1.5 V *(9)*	45	—	95	kΩ

Output Drive Characteristics

Figure 5–1 shows the typical drive strength characteristics of MAX II devices.

Figure 5–1. Output Drive Characteristics of MAX II Devices



Note to Figure 5–1:

(1) The DC output current per pin is subject to the absolute maximum rating of Table 5–1.

I/O Standard Specifications

Table 5–5 through Table 5–10 show the MAX II device family I/O standard specifications.

Table 5–5. 3.3-V LVTTL Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	3.0	3.6	V
V_{IH}	High-level input voltage	—	1.7	4.0	V
V_{IL}	Low-level input voltage	—	–0.5	0.8	V
V_{OH}	High-level output voltage	IOH = –4 mA *(1)*	2.4	—	V
V_{OL}	Low-level output voltage	IOL = 4 mA *(1)*	—	0.45	V

Table 5–6. 3.3-V LVCMOS Specifications (Part 1 of 2)

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	3.0	3.6	V
V_{IH}	High-level input voltage	—	1.7	4.0	V
V_{IL}	Low-level input voltage	—	–0.5	0.8	V

Table 5–6. 3.3-V LVCMOS Specifications (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{OH}	High-level output voltage	V_{CCIO} = 3.0, IOH = –0.1 mA *(1)*	V_{CCIO} – 0.2	—	V
V_{OL}	Low-level output voltage	V_{CCIO} = 3.0, IOL = 0.1 mA *(1)*	—	0.2	V

Table 5–7. 2.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	2.375	2.625	V
V_{IH}	High-level input voltage	—	1.7	4.0	V
V_{IL}	Low-level input voltage	—	–0.5	0.7	V
V_{OH}	High-level output voltage	IOH = –0.1 mA *(1)*	2.1	—	V
		IOH = –1 mA *(1)*	2.0	—	V
		IOH = –2 mA *(1)*	1.7	—	V
V_{OL}	Low-level output voltage	IOL = 0.1 mA *(1)*	—	0.2	V
		IOL = 1 mA *(1)*	—	0.4	V
		IOL = 2 mA *(1)*	—	0.7	V

Table 5–8. 1.8-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	1.71	1.89	V
V_{IH}	High-level input voltage	—	0.65 × V_{CCIO}	2.25 *(2)*	V
V_{IL}	Low-level input voltage	—	–0.3	0.35 × V_{CCIO}	V
V_{OH}	High-level output voltage	IOH = –2 mA *(1)*	V_{CCIO} – 0.45	—	V
V_{OL}	Low-level output voltage	IOL = 2 mA *(1)*	—	0.45	V

Table 5–9. 1.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	1.425	1.575	V
V_{IH}	High-level input voltage	—	0.65 × V_{CCIO}	V_{CCIO} + 0.3 *(2)*	V
V_{IL}	Low-level input voltage	—	–0.3	0.35 × V_{CCIO}	V
V_{OH}	High-level output voltage	IOH = –2 mA *(1)*	0.75 × V_{CCIO}	—	V
V_{OL}	Low-level output voltage	IOL = 2 mA *(1)*	—	0.25 × V_{CCIO}	V

Notes to Table 5–5 through Table 5–9:

(1) This specification is supported across all the programmable drive strength settings available for this I/O standard, as shown in the *MAX II Architecture* chapter (*I/O Structure section*) in the *MAX II Device Handbook*.

(2) This maximum V_{IH} reflects the JEDEC specification. The MAX II input buffer can tolerate a V_{IH} maximum of 4.0, as specified by the V_I parameter in Table 5–2.

Power-Up Timing

Table 5–12 shows the power-up timing characteristics for MAX II devices.

Table 5–12. MAX II Power-Up Timing

Symbol	Parameter	Device	Min	Typ	Max	Unit
t_{CONFIG} *(1)*	The amount of time from when minimum V_{CCINT} is reached until the device enters user mode *(2)*	EPM240	—	—	200	µs
		EPM570	—	—	300	µs
		EPM1270	—	—	300	µs
		EPM2210	—	—	450	µs

Notes to Table 5–12:

(1) Table 5–12 values apply to commercial and industrial range devices. For extended temperature range devices, the t_{CONFIG} maximum values are as follows:

Device	Maximum
EPM240	300 µs
EPM570	400 µs
EPM1270	400 µs
EPM2210	500 µs

(2) For more information about POR trigger voltage, refer to the *Hot Socketing and Power-On Reset in MAX II Devices* chapter in the *MAX II Device Handbook*.

Power Consumption

Designers can use the Altera® PowerPlay Early Power Estimator and PowerPlay Power Analyzer to estimate the device power.

For more information about these power analysis tools, refer to the *Understanding and Evaluating Power in MAX II Devices* chapter in the *MAX II Device Handbook* and the *PowerPlay Power Analysis* chapter in volume 3 of the *Quartus II Handbook*.

Timing Model and Specifications

MAX II devices timing can be analyzed with the Altera Quartus® II software, a variety of popular industry-standard EDA simulators and timing analyzers, or with the timing model shown in Figure 5–2.

MAX II devices have predictable internal delays that enable the designer to determine the worst-case timing of any design. The software provides timing simulation, point-to-point delay prediction, and detailed timing analysis for device-wide performance evaluation.

Table 5–21. UFM Block Internal Timing Microparameters (Part 3 of 3)

Symbol	Parameter	MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t_{OE}	Delay from data register clock to data register output	180	—	180	—	180	—	180	—	180	—	180	—	ns
t_{RA}	Maximum read access time	—	65	—	65	—	65	—	65	—	65	—	65	ns
t_{OSCS}	Maximum delay between the OSC_ENA rising edge to the erase/program signal rising edge	250	—	250	—	250	—	250	—	250	—	250	—	ns
t_{OSCH}	Minimum delay allowed from the erase/program signal going low to OSC_ENA signal going low	250	—	250	—	250	—	250	—	250	—	250	—	ns

Figure 5–3 through Figure 5–5 show the read, program, and erase waveforms for UFM block timing parameters shown in Table 5–21.

Figure 5–3. UFM Read Waveforms

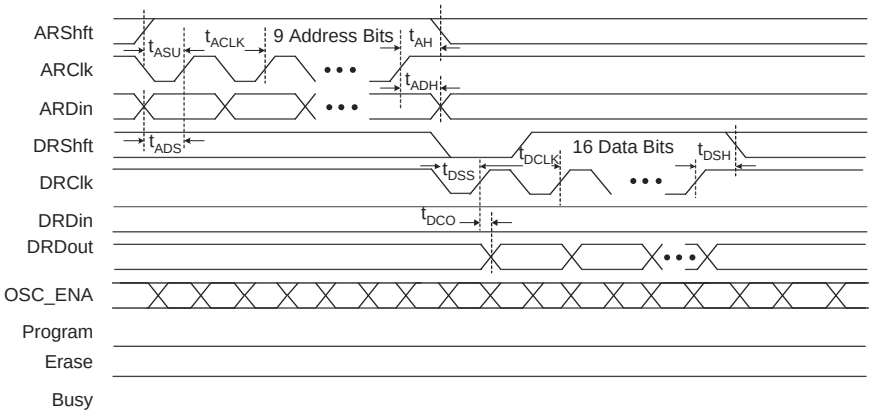


Table 5–26 shows the external I/O timing parameters for EPM2210 devices.

Table 5–26. EPM2210 Global Clock External I/O Timing Parameters

Symbol	Parameter	Condition	MAX II / MAX IIG						Unit
			–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		
			Min	Max	Min	Max	Min	Max	
t_{PD1}	Worst case pin-to-pin delay through 1 look-up table (LUT)	10 pF	—	7.0	—	9.1	—	11.2	ns
t_{PD2}	Best case pin-to-pin delay through 1 LUT	10 pF	—	3.7	—	4.8	—	5.9	ns
t_{SU}	Global clock setup time	—	1.2	—	1.5	—	1.9	—	ns
t_{H}	Global clock hold time	—	0	—	0	—	0	—	ns
t_{CO}	Global clock to output delay	10 pF	2.0	4.6	2.0	6.0	2.0	7.4	ns
t_{CH}	Global clock high time	—	166	—	216	—	266	—	ps
t_{CL}	Global clock low time	—	166	—	216	—	266	—	ps
t_{CNT}	Minimum global clock period for 16-bit counter	—	3.3	—	4.0	—	5.0	—	ns
f_{CNT}	Maximum global clock frequency for 16-bit counter	—	—	304.0 *(1)*	—	247.5	—	201.1	MHz

Note to Table 5–26:

(1) The maximum frequency is limited by the I/O standard on the clock input pin. The 16-bit counter critical delay performs faster than this global clock input pin maximum frequency.

External Timing I/O Delay Adders

The I/O delay timing parameters for I/O standard input and output adders, and input delays are specified by speed grade independent of device density.

Table 5–27 through Table 5–31 show the adder delays associated with I/O pins for all packages. The delay numbers for –3, –4, and –5 speed grades shown in Table 5–27 through Table 5–33 are based on an EPM1270 device target, while –6, –7, and –8 speed grade values are based on an EPM570Z device target. If an I/O standard other than 3.3-V LVTTL is selected, add the input delay adder to the external t_{SU} timing parameters shown in Table 5–23 through Table 5–26. If an I/O standard other than 3.3-V LVTTL with 16 mA drive strength and fast slew rate is selected, add the output delay adder to the external t_{CO} and t_{PD} shown in Table 5–23 through Table 5–26.

Table 5–27. External Timing Input Delay Adders (Part 1 of 2)

I/O Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTL	Without Schmitt Trigger	—	0	—	0	—	0	—	0	—	0	—	0	ps
	With Schmitt Trigger	—	334	—	434	—	535	—	387	—	434	—	442	ps

Table 5–31. MAX II IOE Programmable Delays

Parameter	MAX II / MAX IIG						MAX IIZ						Unit
	–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Input Delay from Pin to Internal Cells = 1	—	1,225	—	1,592	—	1,960	—	1,858	—	2,171	—	2,214	ps
Input Delay from Pin to Internal Cells = 0	—	89	—	115	—	142	—	569	—	609	—	616	ps

Maximum Input and Output Clock Rates

Table 5–32 and Table 5–33 show the maximum input and output clock rates for standard I/O pins in MAX II devices.

Table 5–32. MAX II Maximum Input Clock Rate for I/O

I/O Standard		MAX II / MAX IIG			MAX IIZ			Unit
		–3 Speed Grade	–4 Speed Grade	–5 Speed Grade	–6 Speed Grade	–7 Speed Grade	–8 Speed Grade	
3.3-V LVTTL	Without Schmitt Trigger	304	304	304	304	304	304	MHz
	With Schmitt Trigger	250	250	250	250	250	250	MHz
3.3-V LVCMOS	Without Schmitt Trigger	304	304	304	304	304	304	MHz
	With Schmitt Trigger	250	250	250	250	250	250	MHz
2.5-V LVTTL	Without Schmitt Trigger	220	220	220	220	220	220	MHz
	With Schmitt Trigger	188	188	188	188	188	188	MHz
2.5-V LVCMOS	Without Schmitt Trigger	220	220	220	220	220	220	MHz
	With Schmitt Trigger	188	188	188	188	188	188	MHz
1.8-V LVTTL	Without Schmitt Trigger	200	200	200	200	200	200	MHz
1.8-V LVCMOS	Without Schmitt Trigger	200	200	200	200	200	200	MHz
1.5-V LVCMOS	Without Schmitt Trigger	150	150	150	150	150	150	MHz
3.3-V PCI	Without Schmitt Trigger	304	304	304	304	304	304	MHz

Table 5–33. MAX II Maximum Output Clock Rate for I/O

I/O Standard		MAX II / MAX IIG			MAX IIZ		
		–3 Speed Grade	–4 Speed Grade	–5 Speed Grade	–6 Speed Grade	–7 Speed Grade	–8 Speed Grade
3.3-V LVTTL	304	304	304	304	304	304	MHz
3.3-V LVCMOS	304	304	304	304	304	304	MHz
2.5-V LVTTL	220	220	220	220	220	220	MHz
2.5-V LVCMOS	220	220	220	220	220	220	MHz
1.8-V LVTTL	200	200	200	200	200	200	MHz
1.8-V LVCMOS	200	200	200	200	200	200	MHz
1.5-V LVCMOS	150	150	150	150	150	150	MHz
3.3-V PCI	304	304	304	304	304	304	MHz

JTAG Timing Specifications

Figure 5–6 shows the timing waveforms for the JTAG signals.

Figure 5–6. MAX II JTAG Timing Waveforms

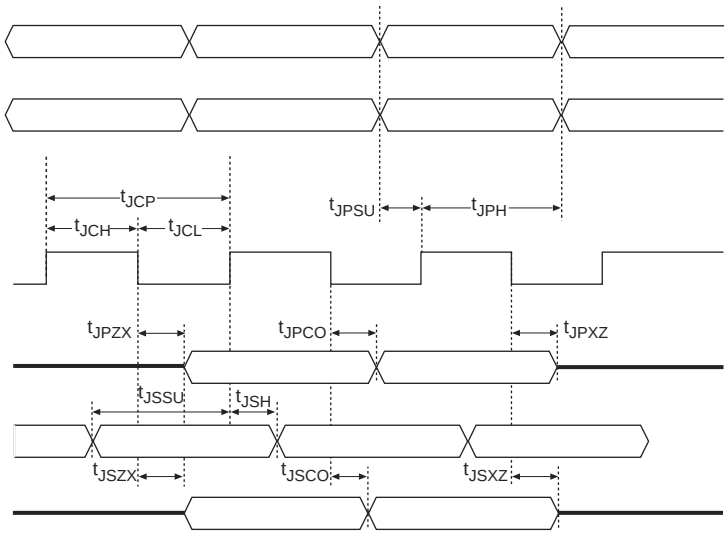


Table 5–34 shows the JTAG Timing parameters and values for MAX II devices.

Table 5–34. MAX II JTAG Timing Parameters (Part 1 of 2)

Symbol	Parameter	Min	Max	Unit
t_{JCP} *(1)*	TCK clock period for V_{CCIO1} = 3.3 V	55.5	—	ns
	TCK clock period for V_{CCIO1} = 2.5 V	62.5	—	ns
	TCK clock period for V_{CCIO1} = 1.8 V	100	—	ns
	TCK clock period for V_{CCIO1} = 1.5 V	143	—	ns
t_{JCH}	TCK clock high time	20	—	ns
t_{JCL}	TCK clock low time	20	—	ns